

Supporting Information

**Highly efficient orange and deep-red organic light emitting diodes
with long operational lifetime using carbazole-quinoline based
bipolar host materials**

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Synthesis of 9-(4-(4-(4-Bromophenyl)quinolin-2-yl)phenyl)-9H-carbazole (CzPPQBr):

A mixture of 1-(4-(9H-carbazol-9-yl)phenyl)ethanone (285 mg, 1.00 mmol), (2-aminophenyl)(4-bromophenyl)methanone (553 mg, 2.00 mmol), diphenyl phosphate (751 mg, 3.00 mmol), and freshly distilled *m*-cresol (1.0 mL) was heated under nitrogen at 140 °C for 12 h. After cooling, the reaction mixture was added to a solution of 10% (v/v) triethylamine in methanol (10.0 mL). The precipitated product was purified by column chromatography (hexane/EtOAc, 10:1) to yield **CzPPQBr** (426 mg, 81.2%). ¹H NMR (400 MHz, CDCl₃, δ): 7.30 (dd, 2H, *J* = 7.2, 7.2 Hz), 7.40-7.52 (m, 7H), 7.69-7.80 (m, 7H), 7.86-7.88 (m, 2H), 8.14 (d, 2H, *J* = 7.2 Hz), 8.27 (d, 1H, *J* = 8.8 Hz), 8.41 (d, 2H, *J* = 8.4 Hz); ¹³C NMR (100 MHz, CDCl₃, δ): 109.8, 119.0, 120.1, 120.4, 122.9, 123.6, 125.3, 125.5, 126.0, 126.8, 127.3, 129.1, 129.9, 130.3, 131.2, 131.9, 137.2, 138.4, 138.9, 140.7, 148.2, 148.9, 156.0; HRMS (EI, *m/z*): [M⁺] calcd for C₃₃H₂₁BrN₂, 524.0888; found, 524.0893.

Synthesis of 9-(4-(6-Bromo-4-phenylquinolin-2-yl)phenyl)-9H-carbazole (CzPPBrQ):

A mixture of 1-(4-(9H-carbazol-9-yl)phenyl)ethanone (285 mg, 1.00 mmol), (2-amino-5-bromophenyl)(phenyl)methanone (553 mg, 2.00 mmol), diphenyl phosphate (751 mg, 3.00 mmol) and freshly distilled *m*-cresol (1.0 mL) was heated under nitrogen at 140 °C for 12 h. After cooling, the reaction mixture was added to a solution of 10% (v/v) triethylamine in methanol (10.0 mL). The precipitated product was purified by column chromatography (hexane/EtOAc, 10:1) to yield **CzPPBrQ** (437 mg, 83.2%). ¹H NMR (400 MHz, CDCl₃, δ): 7.30 (ddd, 2H, *J* = 8.0, 7.6, 1.0 Hz), 7.42 (ddd, 2H, *J* = 8.0, 6.8, 1.2 Hz), 7.48-7.50 (m, 2H), 7.55-7.60 (m, 5H), 7.73 (d, 2H, *J* = 8.4 Hz), 7.82 (dd, 1H, *J* = 9.0, 6.2 Hz), 7.91 (s, 1H), 8.07 (d, 1H, *J* = 3.0 Hz), 8.13-8.16 (m, 3H), 8.41 (d, 2H, *J* = 8.4 Hz); ¹³C NMR (100 MHz, CDCl₃, δ): 109.7, 109.8, 119.9, 120.2, 120.4, 120.7, 123.6, 126.4, 127.1, 127.3, 127.9, 128.8, 128.9, 129.1, 129.4, 131.8, 133.3, 137.6, 138.0, 139.1, 140.6, 148.8, 156.2; HRMS (EI, *m/z*): [M⁺] calcd for C₃₃H₂₁BrN₂, 524.0888; found, 524.0897.

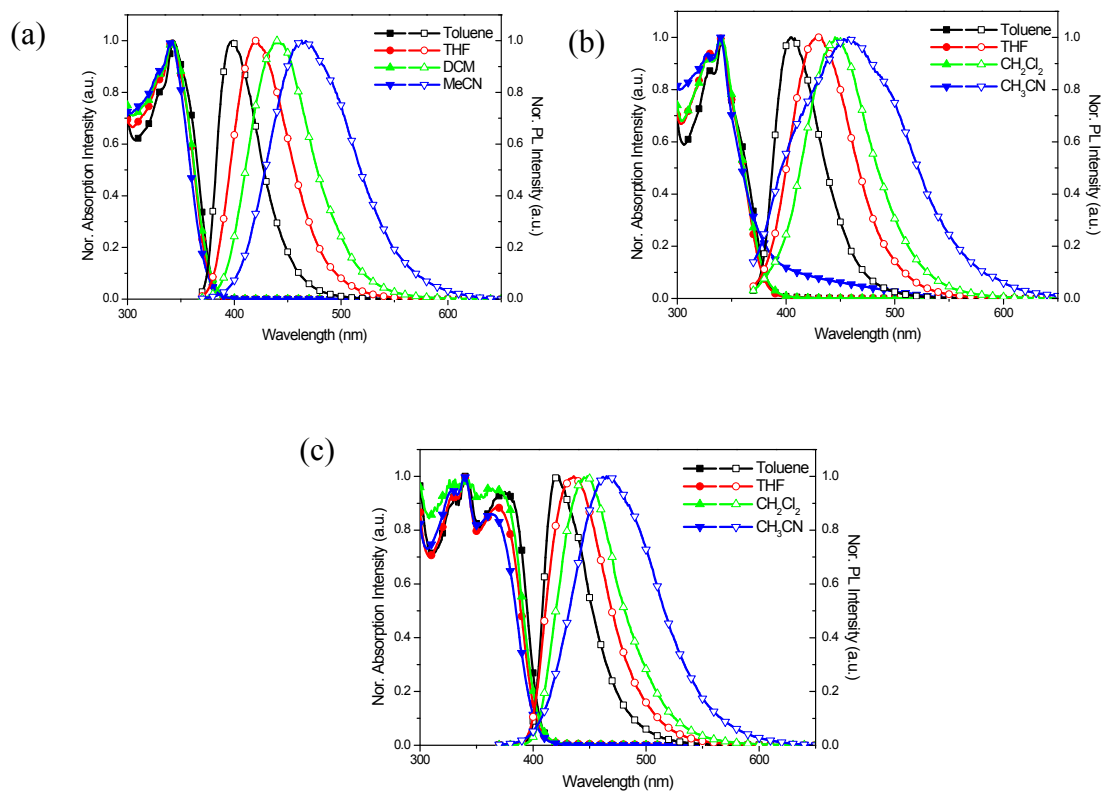


Fig. S1 The absorption and photoluminescence spectra of (a) **CzPPQ**, (b) **CzPPCzQ**, and (c) **CzPPCzQ** in toluene, tetrahydrofuran, dichloromethane and acetonitrile solution (10^{-4} M).

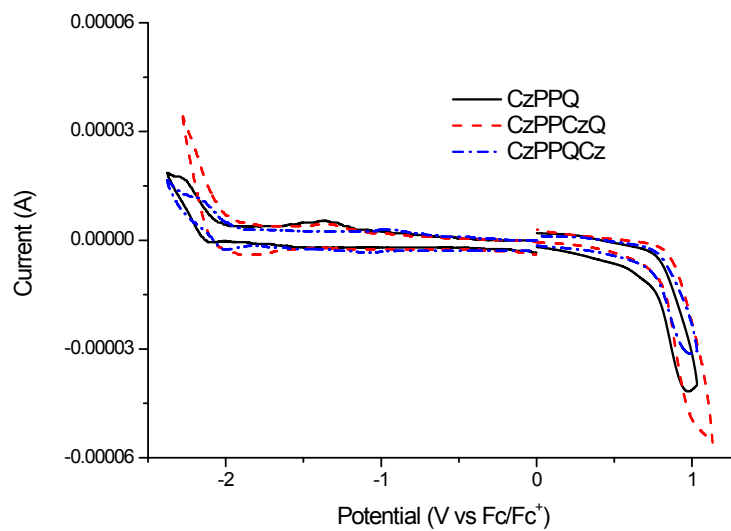
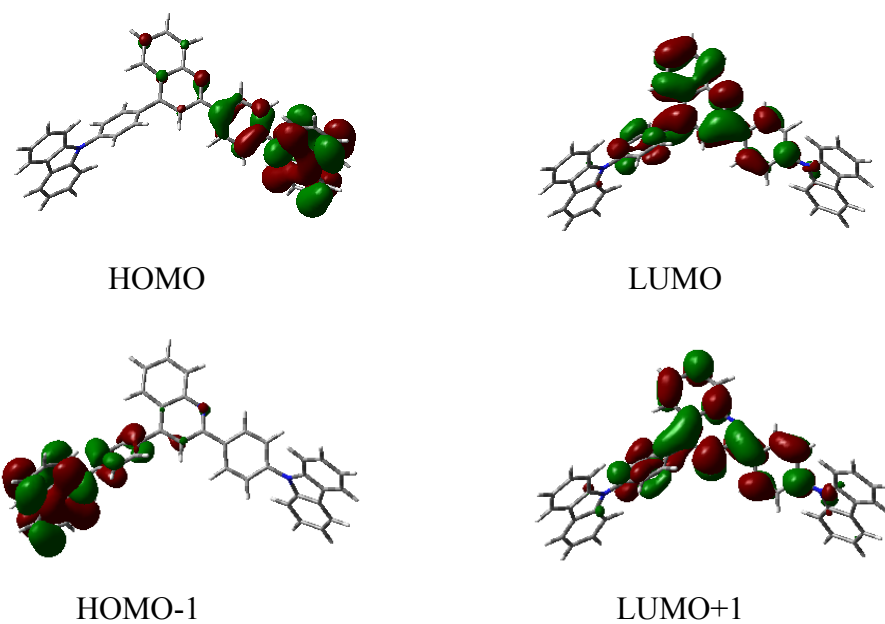


Fig. S2 Cyclic voltammetry measurement of **CzPPQ**, **CzPPCzQ** and **CzPPQCz**.

(a) CzPPCzQ



(b) CzPPQcZ

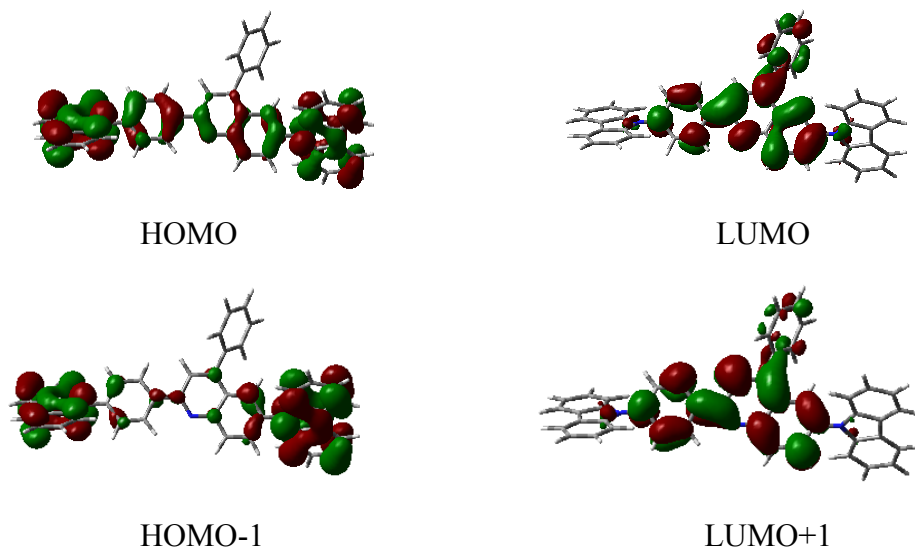


Fig. S3 Calculated electron contour plots of the occupied and unoccupied molecular orbitals of (a) CzPPCzQ and (b) CzPPQcZ

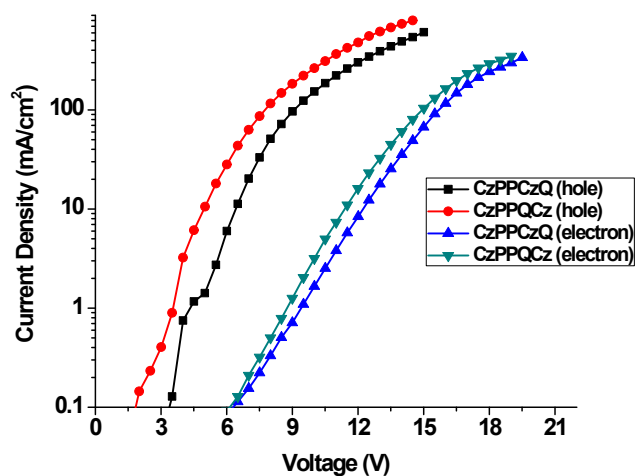


Fig. S4 Current density versus voltage for the hole-only and electron-only devices of **CzPPCzQ** and **CzPPQCz**.

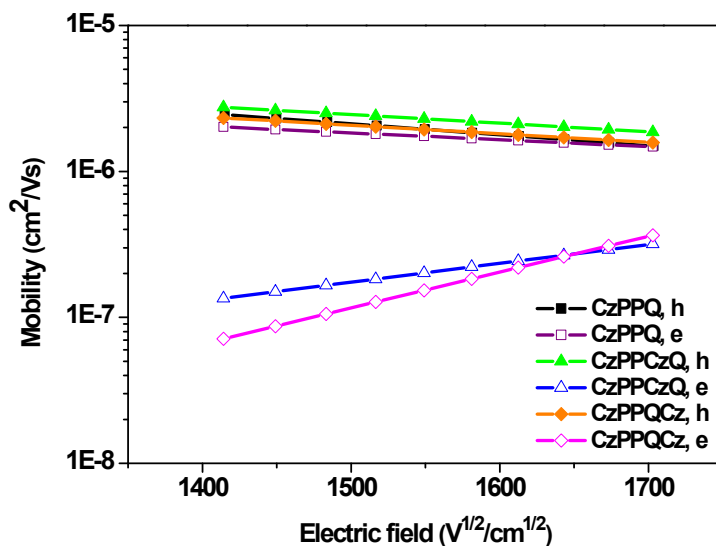


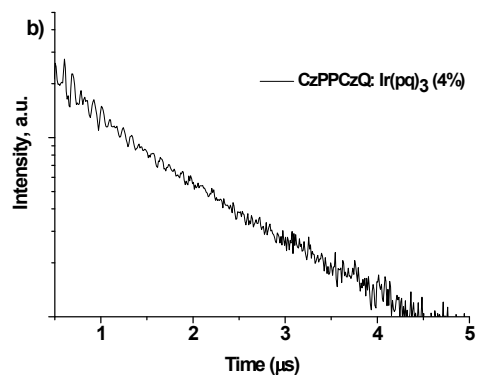
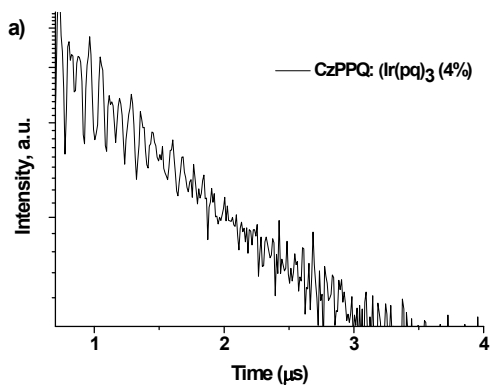
Fig. S5 The relationship of hole and electron mobility vs the electric field. The mobilities of CzPPQ, CzPPCzQ and CzPPQCz were determined by SCLC method. Device structure: ITO/MoO₃ (1)/ CzPPQ or CzPPCzQ or CzPPQCz (50)/ MoO₃ (10)/Al (100) for hole only and ITO/Ca (5)/ CzPPQ or CzPPCzQ or CzPPQCz (50)/ Ca (5)/Al (100) for electron only.

Table S1. Hole and electron mobility of host materials.

Materials	hole mobility (cm^2/Vs) ^a	electron mobility (cm^2/Vs) ^a
CzPPQ	2.13×10^{-6}	1.81×10^{-6}
CzPPCzQ	2.43×10^{-6}	1.16×10^{-7}
CzPPQCz	2.09×10^{-6}	1.70×10^{-7}

^aMobility value at $1500 (\text{V}/\text{cm})^{1/2}$ **Table S2.** Phosphorescence lifetime of $\text{Ir}(\text{piq})_3$ and $\text{Ir}(\text{pq})_3$ co-deposited with **CzPPQ**, **CzPPCzQ** and **CzPPQCz**

Dopants	Host	τ (μs)
$\text{Ir}(\text{pq})_3$	CzPPQ	1.41
$\text{Ir}(\text{pq})_3$	CzPPCzQ	1.06
$\text{Ir}(\text{pq})_3$	CzPPQCz	1.03
$\text{Ir}(\text{piq})_3$	CzPPQ	1.18
$\text{Ir}(\text{piq})_3$	CzPPCzQ	1.04
$\text{Ir}(\text{piq})_3$	CzPPQCz	0.98



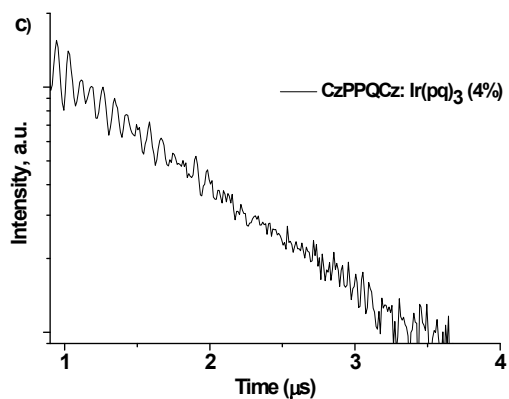


Fig S6. Transient PL decay for 4 wt.% Ir(pq)₃-doped a) CzPPQ, b) CzPPCzQ and c) CzPPQCz thinfilms.

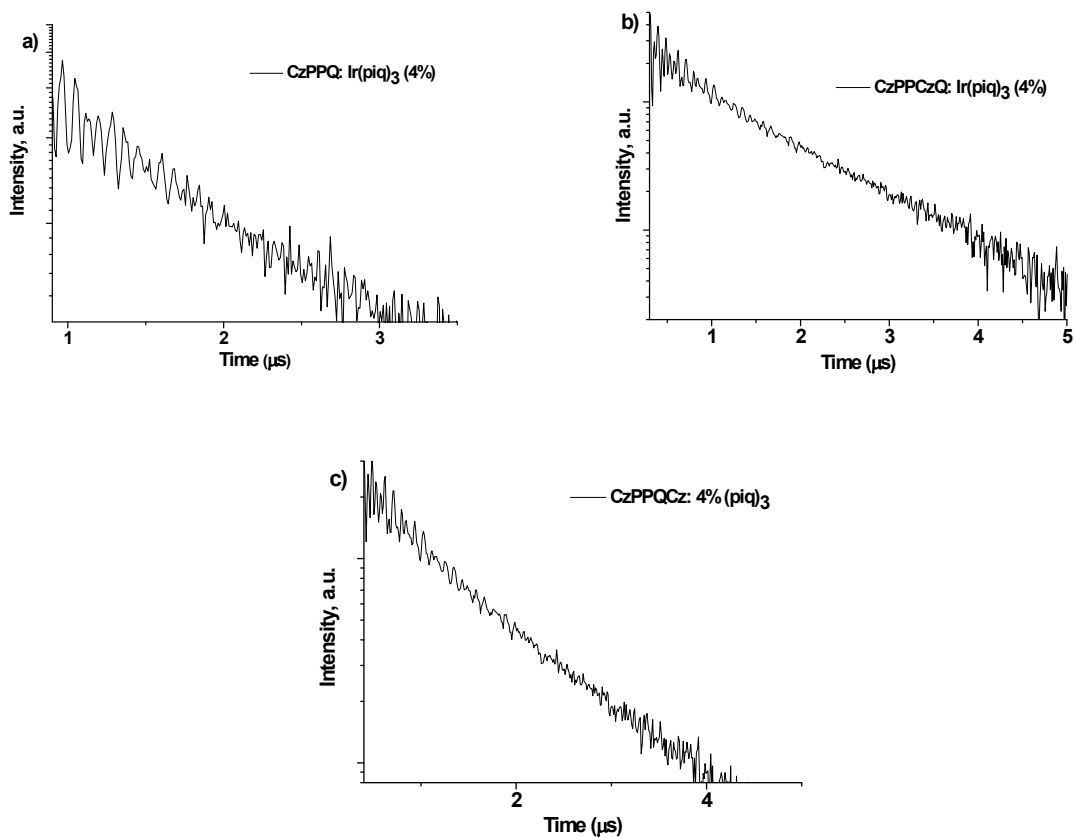


Fig S7. Transient PL decay for 4 wt.% Ir(piq)₃-doped a) CzPPQ, b) CzPPCzQ and c) CzPPQCz thinfilms.

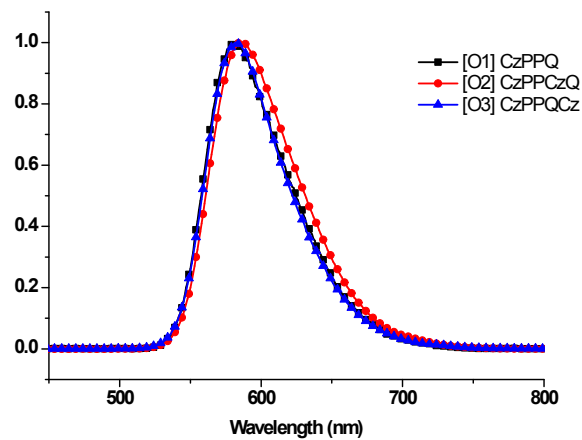


Fig. S8 Electroluminescence spectra of devices O1-O3 at 8V

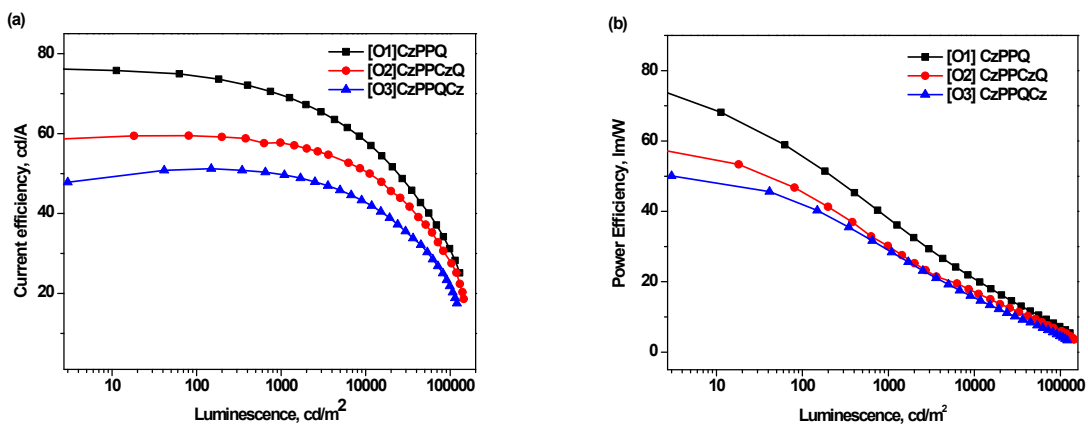


Fig. S9 (a) Luminescence vs current efficiency and (b) Luminescence vs power efficiency curves of devices O1-O3

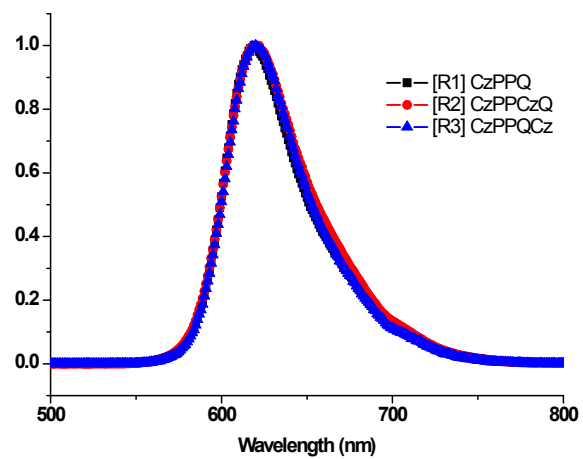


Fig. S10 Electroluminescence spectra of R1-R3 devices at 8V